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Facile fabrication of heterostructure with p-BiOCI nanoflakes and n-ZnO thin film for UV photodetectors

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Abstract: Herein, high-quality n-ZnO film layer on *c*-sapphire and well-crystallized tetragonal p-BiOCI nanoflakes on Cu foil are prepared, respectively. According to the absorption spectra, the bandgaps of n-ZnO and p-BiOCI are confirmed as ~3.3 and ~3.5 eV, respectively. Subsequently, a p-BiOCI/n-ZnO heterostructural photodetector is constructed after a facile mechanical bonding and post annealing process. At –5 V bias, the photocurrent of the device under 350 nm irradiation is ~800 times higher than that in dark, which indicates its strong UV light response characteristic. However, the on/off ratio of In–ZnO–In photodetector is ~20 and the Cu–BiOCI–Cu photodetector depicts very weak UV light response. The heterostructure device also shows a short decay time of 0.95 s, which is much shorter than those of the devices fabricated from pure ZnO thin film and BiOCI nanoflakes. The p-BiOCI/n-ZnO heterojunction photodetector provides a promising pathway to multifunctional UV photodetectors with fast response, high signal-to-noise ratio, and high selectivity.

Key words: ZnO thin film; BiOCI nanoflakes; heterostucture; UV photodetector

Citation: L X Su, W X O yang, and X S Fang, Facile fabrication of heterostructure with p-BiOCI nanoflakes and n-ZnO thin film for UV photodetectors[J]. J. Semicond., 2021, 42(5), 052301. http://doi.org/10.1088/1674-4926/42/5/052301

Supporting Information



Fig. S1. (Color online) The detectivities of the p-BiOCl/n-ZnO photodetector at different negative biases (a) and positive biases (b). Correspondence to: X S Fang, Xiaosheng Fang, Email: xshfang@fudan.edu.cn Received 21 SEPTEMBER 2020; Revised 19 OCTOBER 2020.

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Fig. S2. The spectral responsivities of the p-BiOCl/n-ZnO photodetector under 0 V bias.



Fig. S3. The I-T curve of the p-BiOCl/n-ZnO photodetector under 350 nm (0.304 mW/cm²) illumination at 0 V bias.